TinyLogic UHS Dual Inverter with Schmitt Trigger Inputs

NC7WZ14

Description

The NC7WZ14 is a dual inverter with Schmitt trigger input from **onsemi**'s Ultra−High Speed (UHS) Series of TinyLogic. The device is fabricated with advanced CMOS technology to achieve ultra−high speed with high output drive while maintaining low static power dissipation over a very broad V_{CC} operating range. The device is specified to operate over the 1.65 V to 5.5 V V_{CC} range. The inputs and outputs are high−impedance when V_{CC} is 0 V. Inputs tolerate voltages up to 5.5 V independent of V_{CC} operating voltage. Schmitt trigger inputs achieve typically 1 V hysteresis between the positive−and negative−going input threshold voltage at 5 V.

Features

- Ultra High−Speed: t_{PD} = 3.2 ns (Typical) into 50 pF at 5 V
- High Output Drive: ±24 mA at 3 V V_{CC}
- Broad V_{CC} Operating Range: 1.65 V to 5.5 V
- Matches Performance of LCX when Operated at 3.3 V V_{CC}
- Power Down High Impedance Inputs / Outputs
- Over−Voltage Tolerance Inputs Facilitate 5 V to 3 V Translation
- Proprietary Noise / EMI Reduction Circuitry
- Ultra−Small MicroPak™ Packages
- Space−Saving SC−88 Package
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

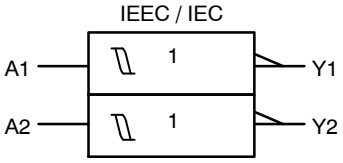
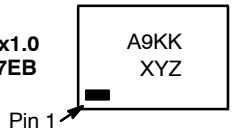


Figure 1. Logic Symbol

MARKING DIAGRAMS

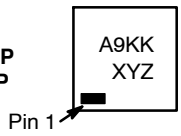


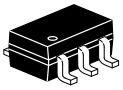
SIP6 1.45x1.0
CASE 127EB



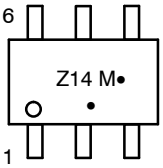


UDFN6
1.0X1.0, 0.35P
CASE 517DP





SC−88
CASE 419B−02



A9, Z14	= Specific Device Code
KK	= 2−Digit Lot Run Traceability Code
XY	= 2−Digit Date Code Format
Z	= Assembly Plant Code
M	= Date Code
•	= Pb−Free Package
	(Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

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Pin Configurations

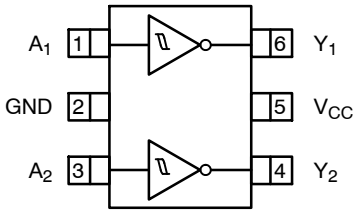


Figure 2. SC−88 (Top View)

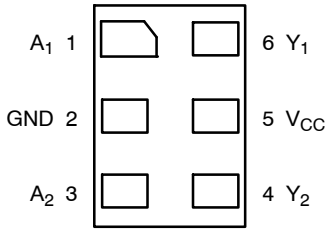
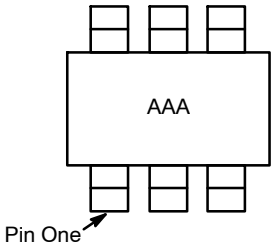


Figure 3. MicroPak (Top Through View)



NOTES:
1. AAA represents Product Code Top Mark (*see Ordering Information*).
2. Orientation of Top Mark determines Pin One location. Read the top mark left to right, pin one is the lower left pin.

Figure 4. SC−88 Pin 1 Orientation

PIN DEFINITIONS

Pin # SC−88	Pin # MicroPak	Name	Description
1	1	A_1	Input
2	2	GND	Ground
3	3	A_2	Input
4	4	Y_2	Output
5	5	V_{CC}	Supply Voltage
6	6	Y_1	Output

FUNCTION TABLE ($Y = \overline{A}$)

Input	Output
A	**Y**
L	H
H	L

H = HIGH Logic Level
L = LOW Logic Level

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage		−0.5	6.5	V
V_{IN}	DC Input Voltage		−0.5	6.5	V
V_{OUT}	DC Output Voltage		−0.5	6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < 0 V	−	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < 0 V	−	−50	mA
I_{OUT}	DC Output Current		−	±50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current		−	±100	mA
T_{STG}	Storage Temperature Range		−65	+150	°C
T_J	Junction Temperature Under Bias		−	+150	°C
T_L	Junction Lead Temperature (Soldering, 10 Seconds)		−	+260	°C
P_D	Power Dissipation	SC−88	−	332	mW
		MicroPak−6	−	812	
		MicroPak2™−6	−	812	
ESD	Human Body Model, JEDEC: JESD22−A114		−	4000	V
	Charge Device Model, JEDEC: JESD22−C101		−	2000	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply Voltage Operating		1.65	5.50	V
	Supply Voltage Data Retention		1.5	5.5	
V_{IN}	Input Voltage		0	5.5	V
V_{OUT}	Output Voltage		0	V_{CC}	V
T_A	Operating Temperature	SC−88	−40	+125	°C
		MicroPak−6	−40	+85	
		MicroPak2−6	−40	+85	
θ_{JA}	Thermal Resistance	SC−88	−	377	°C/W
		MicroPak−6	−	154	
		MicroPak2−6	−	154	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTICAL CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	Conditions	T_A = +25°C			T_A = −40 to +85°C		T_A = −40 to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_P	Positive Threshold Voltage	1.65		−	−	1.40	−	1.40	−	1.40	V
		1.80		−	−	1.50	−	1.50	−	1.50	
		2.30		−	−	1.80	−	1.80	−	1.80	
		3.00		−	−	2.20	−	2.20	−	2.20	
		4.50		−	−	3.10	−	3.10	−	3.20	
		5.50		−	−	3.60	−	3.60	−	3.70	

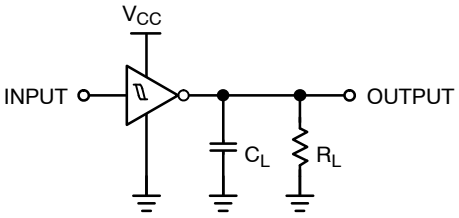
DC ELECTICAL CHARACTERISTICS (continued)

Symbol	Parameter	V_{CC} (V)	Conditions	T_A = +25°C			T_A = −40 to +85°C		T_A = −40 to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_N	Negative Threshold Voltage	1.65		0.20	0.50	–	0.20	–	0.30	–	V
		1.80		0.25	0.56	–	0.25	–	0.35	–	
		2.30		0.40	0.75	–	0.40	–	0.50	–	
		3.00		0.60	0.98	–	0.60	–	0.70	–	
		4.50		1.00	1.42	–	1.00	–	1.10	–	
		5.50		1.20	1.68	–	1.20	–	1.40	–	
V_H	Hysteresis Voltage	1.65		0.10	0.48	0.90	0.10	0.90	0.10	0.90	V
		1.80		0.15	0.51	1.00	0.15	1.00	0.15	1.00	
		2.30		0.25	0.62	1.10	0.25	1.10	0.25	1.10	
		3.00		0.40	0.76	1.20	0.40	1.20	0.40	1.20	
		4.50		0.60	1.01	1.50	0.60	1.50	0.60	1.50	
		5.50		0.70	1.20	1.70	0.70	1.70	0.70	1.70	
V_{OH}	HIGH Level Output Voltage	1.65	V_{IN} = V_P or V_N, I_{OH} = −100 μA	1.55	1.65	–	1.55	–	1.55	–	V
		1.80		1.70	1.80	–	1.70	–	1.70	–	
		2.30		2.20	2.30	–	2.20	–	2.20	–	
		3.00		2.90	3.00	–	2.90	–	2.90	–	
		4.50		4.40	4.50	–	4.40	–	4.40	–	
		1.65	I_{OH} = −4 mA	1.29	1.52	–	1.29	–	1.26	–	
		2.30	I_{OH} = −8 mA	1.90	2.14	–	1.90	–	1.80	–	
		3.00	I_{OH}= −16 mA	2.40	2.75	–	2.40	–	2.30	–	
		3.00	I_{OH}= −24 mA	2.30	2.62	–	2.30	–	2.20	–	
		4.50	I_{OH}= −32 mA	3.80	4.13	–	3.80	–	3.70	–	
V_{OL}	LOW Level Output Voltage	1.65	V_{IN} = V_P or V_N, I_{OL} = 100 μA	–	0.00	0.10	–	0.10	–	0.10	V
		1.80		–	0.00	0.10	–	0.10	–	0.10	
		2.30		–	0.00	0.10	–	0.10	–	0.10	
		3.00		–	0.00	0.10	–	0.10	–	0.10	
		4.50		–	0.00	0.10	–	0.10	–	0.10	
		1.65	I_{OL} = 4 mA	–	0.08	0.24	–	0.24	–	0.26	
		2.30	I_{OL} = 8 mA	–	0.10	0.30	–	0.30	–	0.32	
		3.00	I_{OL} = 16 mA	–	0.16	0.40	–	0.40	–	0.43	
		3.00	I_{OL} = 24 mA	–	0.24	0.55	–	0.55	–	0.60	
		4.50	I_{OL} = 32 mA	–	0.25	0.55	–	0.55	–	0.60	
I_{IN}	Input Leakage Current	1.65 to 5.5	V_{IN} = 5.5 V, GND	–	–	±0.1	–	±1.0	–	±2.0	μA
I_{OFF}	Power Off Leakage Current	0	V_{IN} or V_{OUT} = 5.5 V	–	–	1	–	10	–	20	μA
I_{CC}	Quiescent Supply Current	1.65 to 5.5	V_{IN} = 5.5 V, GND	–	–	1.0	–	10	–	20	μA

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	Conditions	T_A = +25°C			T_A = −40 to +85°C		T_A = −40 to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay (Figure 5, 6)	1.65	C_L = 15 pF, R_L = 1 MΩ,	–	7.6	13.1	–	14.5	–	14.7	ns
		1.80		–	6.3	10.9	–	12.0	–	12.3	
		2.50 ±0.20		–	4.3	7.4	–	8.1	–	8.4	
		3.30 ±0.30		–	3.3	5.0	–	5.5	–	5.8	
		5.00 ±0.50		–	2.7	4.1	–	4.5	–	4.8	
		3.30 ±0.30	C_L = 50 pF, R_L = 500 Ω,	–	4.0	6.0	–	6.6	–	6.9	
		5.00 ±0.50		–	3.2	4.9	–	5.4	–	5.7	
C_{IN}	Input Capacitance	0.00		–	2.5	–	–	–	–	–	pF
C_{PD}	Power Dissipation Capacitance (Note 4) (Figure 7)	3.30		–	11.0	–	–	–	–	–	pF
		5.00		–	12.5	–	–	–	–	–	

4. C_{PD} is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I_{CCD}) at no output loading and operating at 50% duty cycle. C_{PD} is related to I_{CCD} dynamic operating current by the expression: $I_{CCD} = (C_{PD})\ (V_{CC})\ (f_{IN}) + (I_{CC}static)$.



NOTE:
5. C_L includes load and stray capacitance; Inputs PRR = 1.0 MHz, t_W = 500 ns.

Figure 5. AC Test Circuit

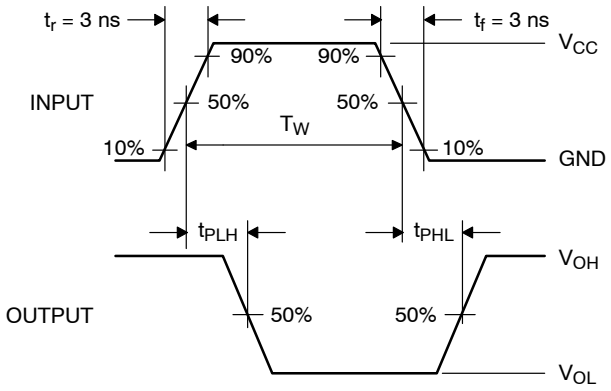
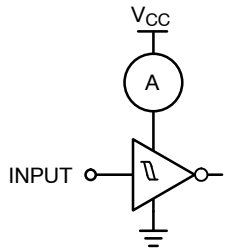


Figure 6. AC Waveforms



NOTE:
6. Input = AC Waveform; $t_r = t_f$ = 1.8 ns; PRR = variable; Duty Cycle = 50%.

Figure 7. I_{CCD} Test Circuit

ORDERING INFORMATION

Device	Operating Temperature	Top Mark	Packages	Shipping†
NC7WZ14P6X	−40 to +85°C	Z14	6−Lead SC70, EIAJ SC−88, 1.25 mm Wide	3000 / Tape & Reel
NC7WZ14P6X−L22347	−40 to +125°C	Z14	6−Lead SC70, EIAJ SC−88, 1.25 mm Wide	3000 / Tape & Reel
NC7WZ14EP6X	−40 to +125°C	Z14	6−Lead SC70, EIAJ SC−88, 1.25 mm Wide	3000 / Tape & Reel
NC7WZ14L6X	−40 to +85°C	A9	6−Lead MicroPak, 1.00 mm Wide	5000 / Tape & Reel
NC7WZ14L6X−L22175	−40 to +85°C	A9	6−Lead MicroPak, 1.00 mm Wide	5000 / Tape & Reel
NC7WZ14FHX	−40 to +85°C	A9	6−Lead, MicroPak2, 1x1 mm Body, .35 mm Pitch	5000 / Tape & Reel
NC7WZ14FHX−L22175	−40 to +85°C	A9	6−Lead, MicroPak2, 1x1 mm Body, .35 mm Pitch	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

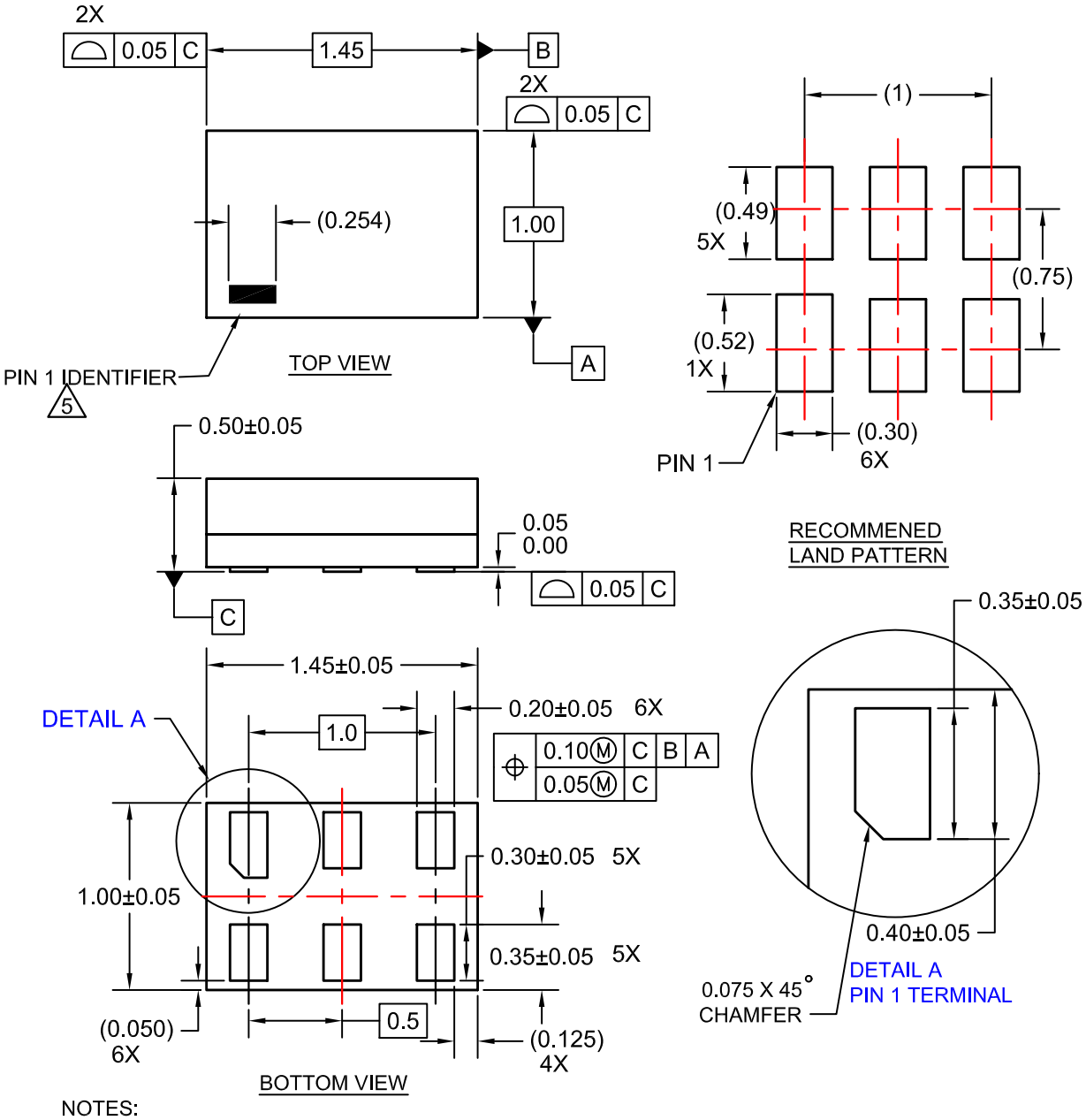
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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

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CASE 127EB
ISSUE O

DATE 31 AUG 2016



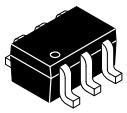
NOTES:

1. CONFORMS TO JEDEC STANDARD MO-252 VARIATION UAAD
2. DIMENSIONS ARE IN MILLIMETERS
3. DRAWING CONFORMS TO ASME Y14.5M-2009
4. PIN ONE IDENTIFIER IS 2X LENGTH OF ANY OTHER LINE IN THE MARK CODE LAYOUT.

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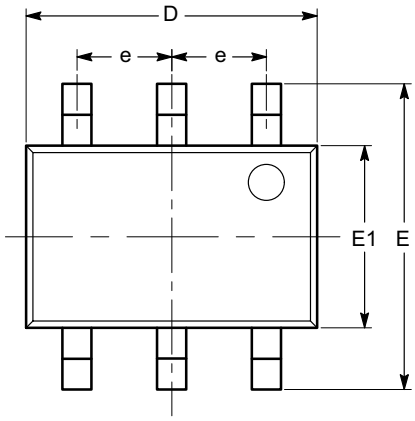
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



1

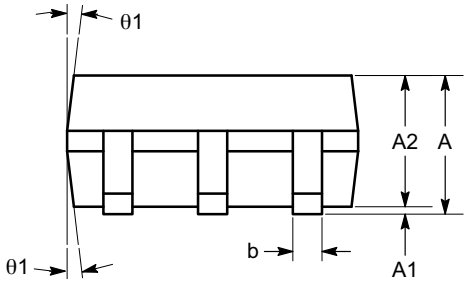
SC−88 (SC−70 6 Lead), 1.25x2
CASE 419AD
ISSUE A

DATE 07 JUL 2010

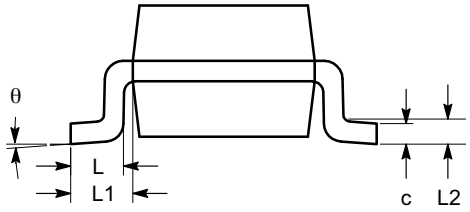


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	0.80		1.10
A1	0.00		0.10
A2	0.80		1.00
b	0.15		0.30
c	0.10		0.18
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
e		0.65 BSC	
L	0.26	0.36	0.46
L1		0.42 REF	
L2		0.15 BSC	
θ	0°		8°
θ1	4°		10°



SIDE VIEW



END VIEW

Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-203.

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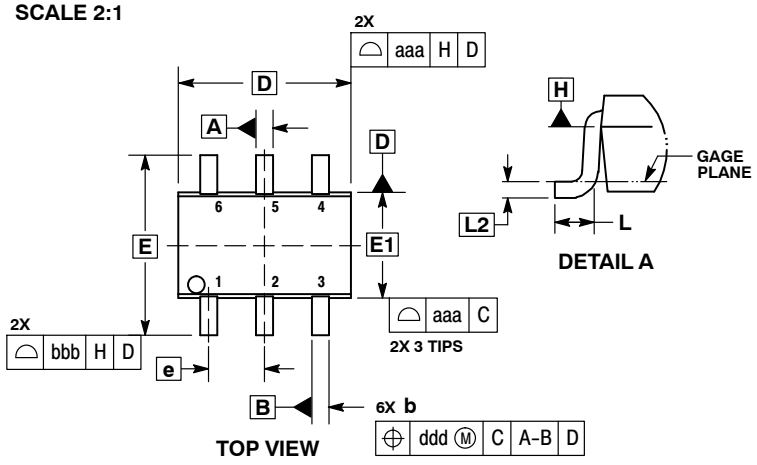
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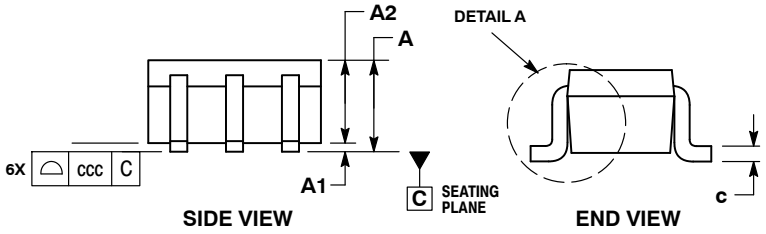
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SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

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SCALE 2:1

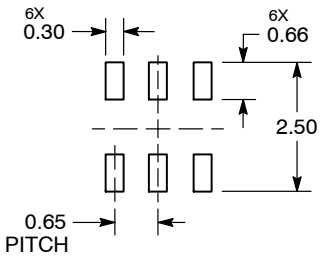




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

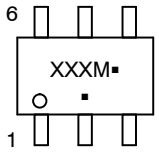
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

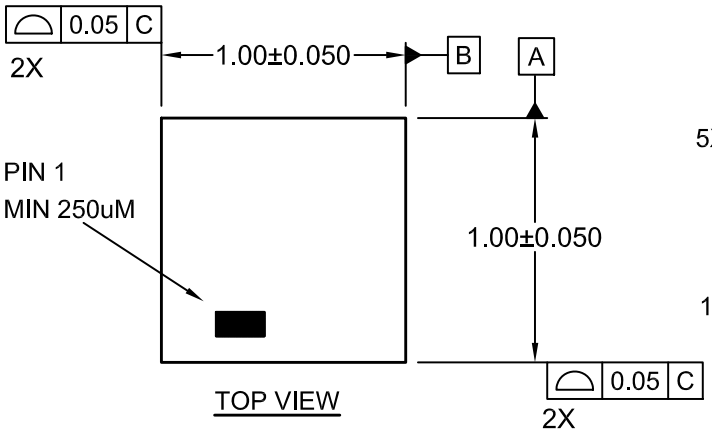
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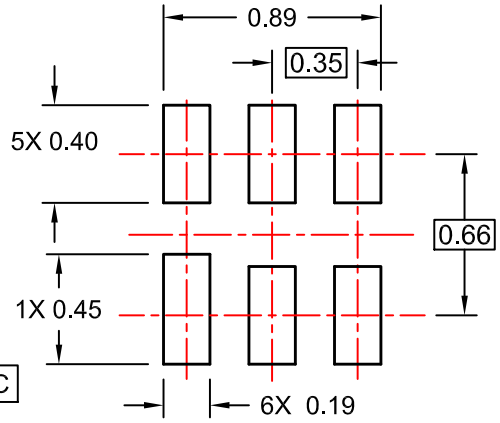
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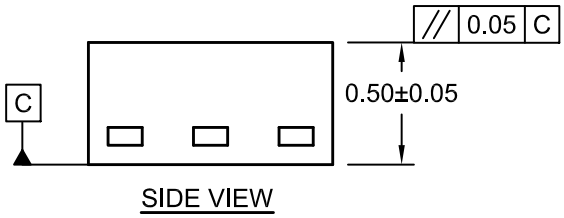
UDFN6 1.0X1.0, 0.35P
CASE 517DP
ISSUE O

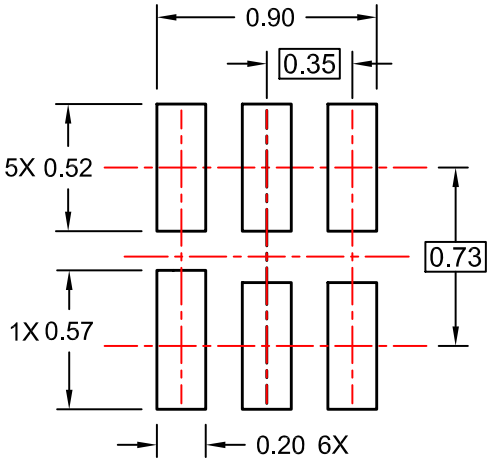
DATE 31 AUG 2016



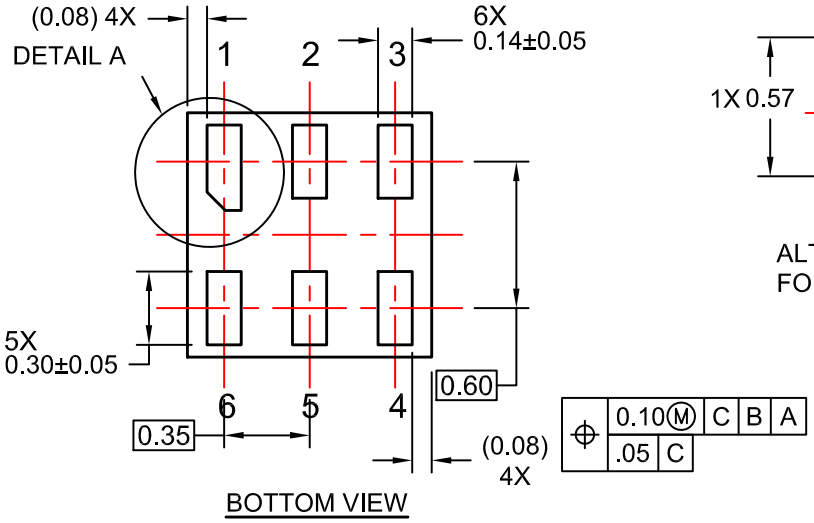


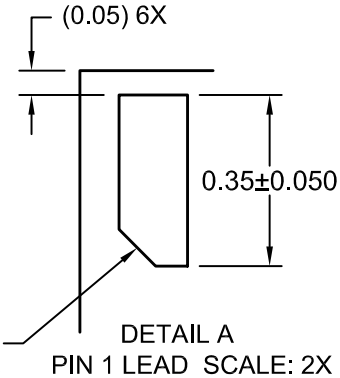
RECOMMENDED LAND PATTERN
FOR SPACE CONSTRAINED PCB





ALTERNATIVE LAND PATTERN
FOR UNIVERSAL APPLICATION





NOTES:

A. COMPLIES TO JEDEC MO-252 STANDARD
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009

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